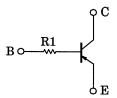
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

# RN2131F,RN2132F

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

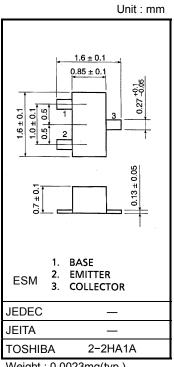
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1131F, RN1132F •

#### **Equivalent Circuit**



#### Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-100	mA
Collector power dissipation	P <sub>C</sub>	100	mW
Junction temperature	Тј	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

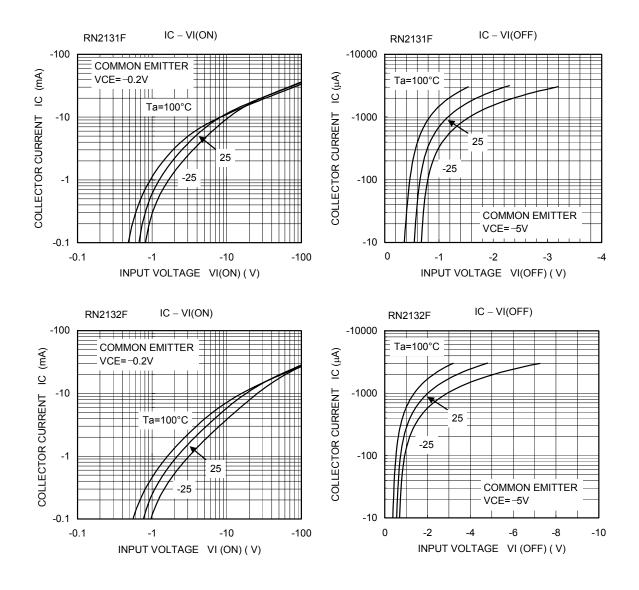


Weight : 0.0023mg(typ.)

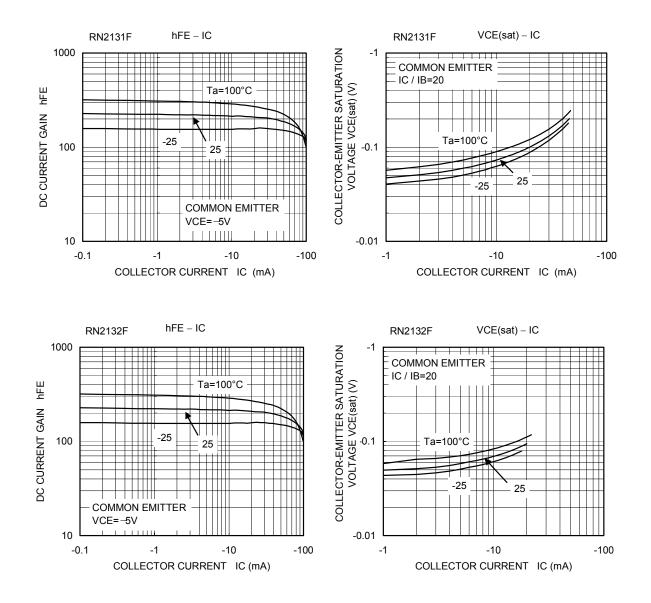
### Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	_	$V_{CB} = -50V, I_E = 0$	_	_	-100	nA
Emitter cut-off current		I <sub>EBO</sub>	—	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
DC current gain		h <sub>FE</sub>	—	$V_{CE} = -5V$ , $I_C = -1mA$	120	—	700	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	_	I <sub>C</sub> = −5mA, I <sub>B</sub> = −0.25mA	_	-0.1	-0.3	V
Transition frequency		f <sub>T</sub>	—	V <sub>CE</sub> = −10V, I <sub>C</sub> = −5mA	-	200	—	MHz
Collector output capacitance		C <sub>ob</sub>	—	$V_{CB}$ = -10V, I <sub>E</sub> = 0, f = 1MH <sub>z</sub>	—	3	—	pF
Input resistor	RN2131F	R1	_	_	70	100	130	kΩ
	RN2132F				140	200	260	

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## **TOSHIBA**

Type Name	Marking	
RN2131F	Type Name Y 3	
RN2132F	Type Name Y 4	

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